

PJD14P06A-AU

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-14 A

Features

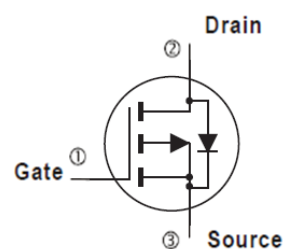
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-6A < 110m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-3A < 130m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0105 ounces, 0.297grams



TO-252AA



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (Note 4)	$T_C=25^\circ\text{C}$	I_D	-14	A
	$T_C=100^\circ\text{C}$		-9	
Pulsed Drain Current (Note 1)	$T_C=25^\circ\text{C}$	I_{DM}	-42	
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	40	W
	$T_C=100^\circ\text{C}$		16	
Continuous Drain Current (Note 4)	$T_A=25^\circ\text{C}$	I_D	-3.2	A
	$T_A=70^\circ\text{C}$		-2.5	
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	2.0	W
	$T_A=70^\circ\text{C}$		1.3	
Single Pulse Avalanche Energy (Note 6)		E_{AS}	20	mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	3.1	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature



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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.7	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-6A	-	87	110	mΩ
		V _{GS} =-4.5V, I _D =-3A	-	110	130	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic (Note 7)						
Total Gate Charge	Q _g	V _{DS} =-30V, I _D =-4A, V _{GS} =-10V (Note 2,3)	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	
Gate-Drain Charge	Q _{gd}		-	3	-	
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, f=1MHZ	-	785	-	pF
Output Capacitance	C _{oss}		-	175	-	
Reverse Transfer Capacitance	C _{rss}		-	112	-	
Turn-On Delay Time	td _(on)	V _{DS} =-30V, RL=30Ω, V _{GS} =-10V, R _G =6.2Ω (Note 2,3)	-	8	-	ns
Turn-On Rise Time	tr		-	15	-	
Turn-Off Delay Time	td _(off)		-	43	-	
Turn-Off Fall Time	tf		-	8.4	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	Is	---	-	-	-14	A
Reverse Recovery Time	VSD	Is=-1A, VGS=0V	-	-0.76	-1	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J = 25°C.
4. The maximum current rating is package limited.
5. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. L=0.1mH, I_{AS}=-20A, V_{GS}=-10V, V_{DS}=-25V, R_G=25 ohm.
7. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

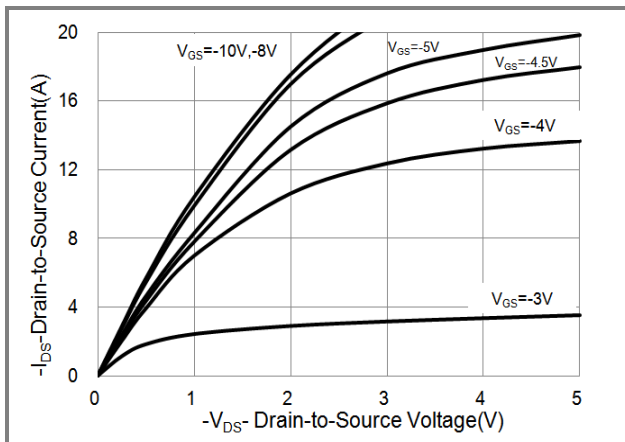


Fig.1 On-Region Characteristics

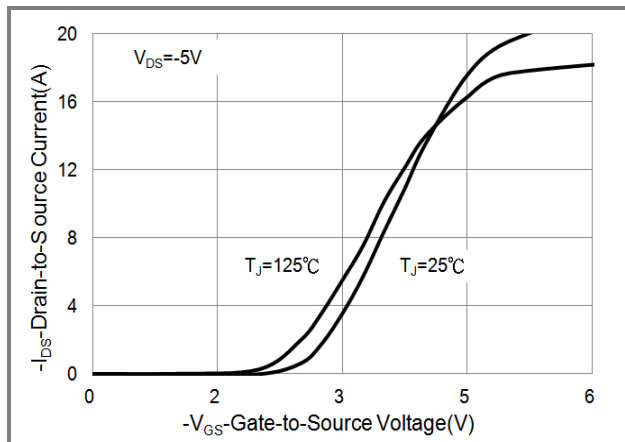


Fig.2 Transfer Characteristics

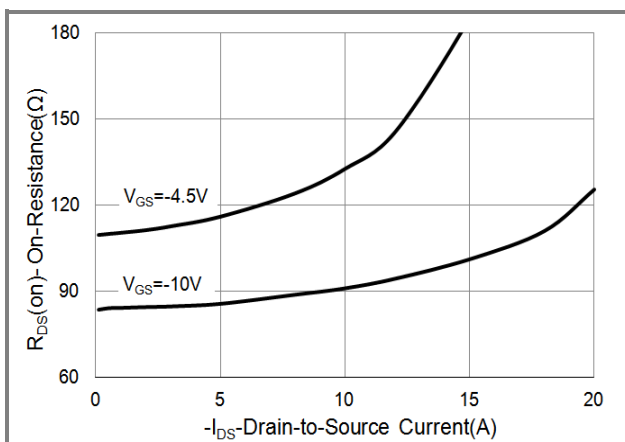


Fig.3 On-Resistance vs. Drain Current

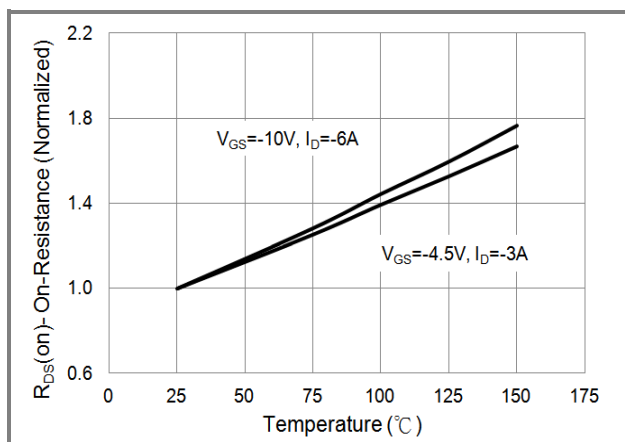


Fig.4 On-Resistance vs. Junction temperature

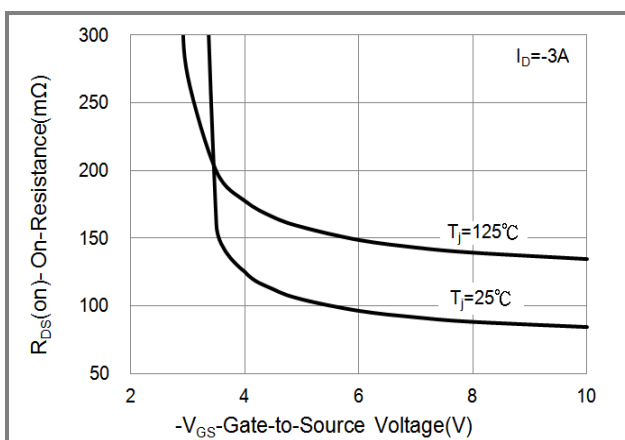


Fig.5 On-Resistance Variation with V_{GS}

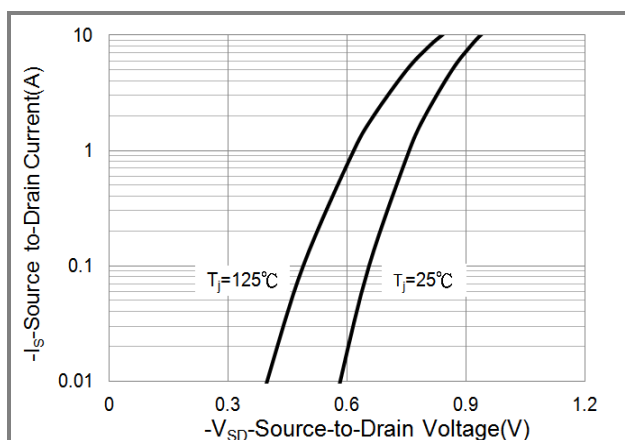


Fig.6 Body Diode Characteristics

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TYPICAL CHARACTERISTIC CURVES

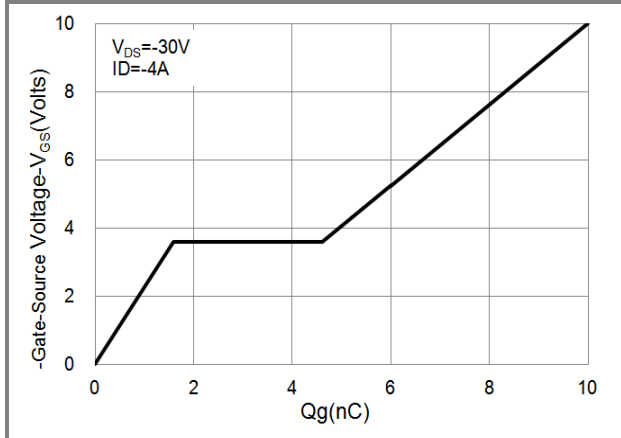


Fig.7 Gate-Charge Characteristics

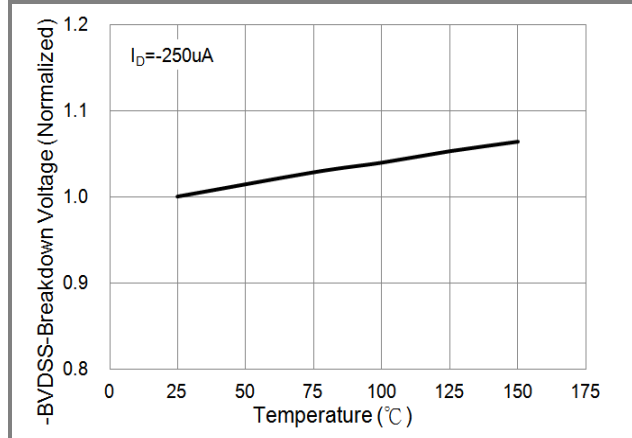


Fig.8 Breakdown Voltage Variation vs. Temperature

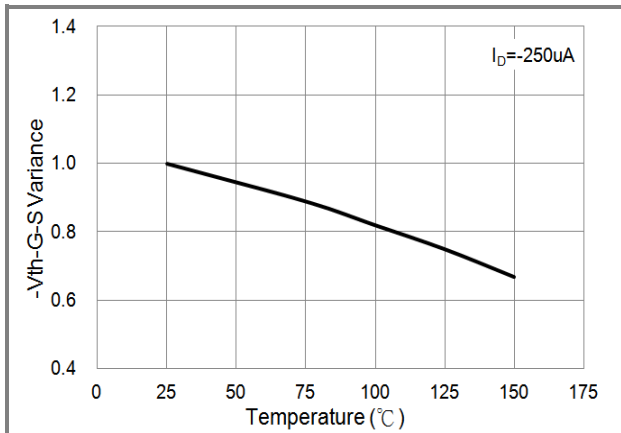


Fig.9 Threshold Voltage Variation with Temperature

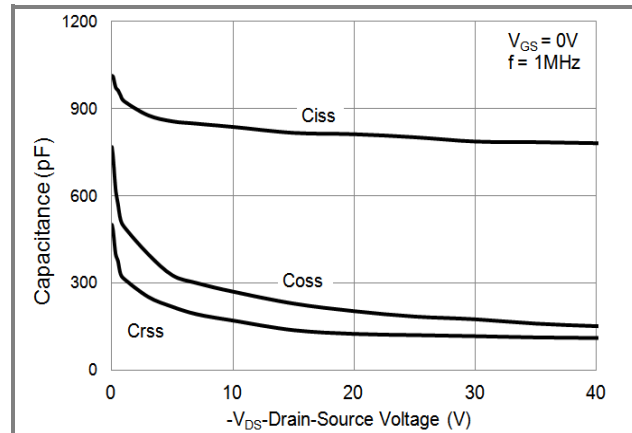


Fig.10 Capacitance vs. Drain-Source Voltage

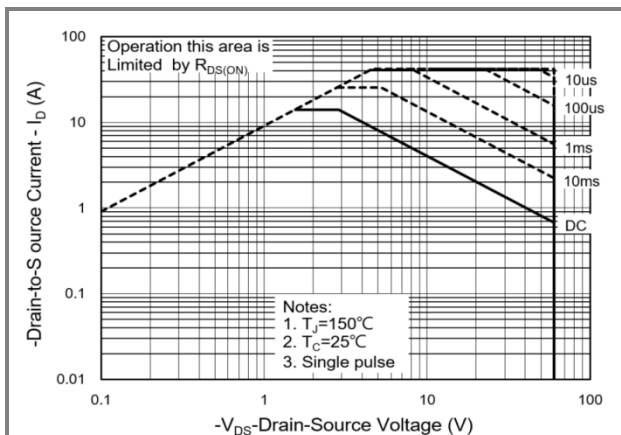


Fig.11 Maximum Safe Operating Area

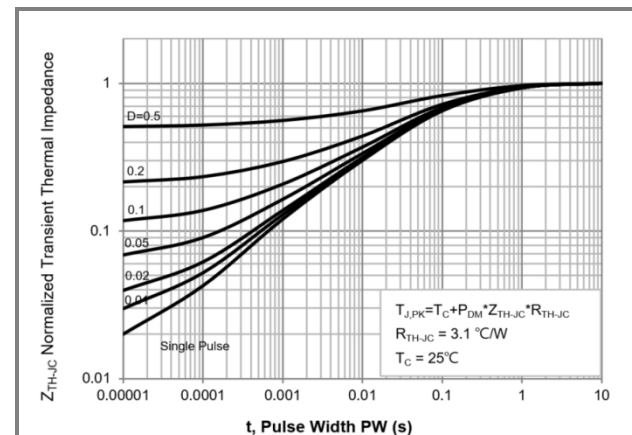


Fig.12 Normalized Thermal Transient Impedance

Part No. Packing Code Version

Packaging Information & Mounting Pad Layout

Unit: inch(mm)





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